



**CHENMKO ENTERPRISE CO.,LTD**

**CHT3055ZPT**

**SURFACE MOUNT  
NPN SILICON Transistor**

VOLTAGE 60 Volts CURRENT 6 Ampere

Lead free devices

**APPLICATION**

- \* Telephony and professional communication equipment.
- \* Other switching applications.

**FEATURE**

- \* Small flat package. ( SC-73/SOT-223 )
- \* Suitable for high packing density.
- \* High saturation current capability.

**CONSTRUCTION**

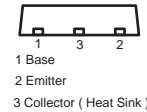
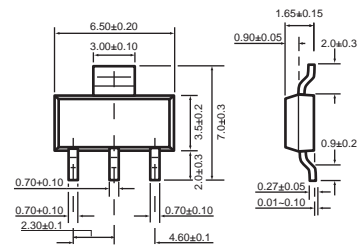
\*NPN SILICON Transistor

**MARKING**

\* ZDN



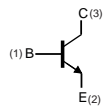
SC-73/SOT-223



Dimensions in millimeters

SC-73/SOT-223

**CIRCUIT**



**LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V <sub>CB0</sub>	collector-base voltage	open emitter	—	100	V
V <sub>CEO</sub>	collector-emitter voltage	open base	—	60	V
V <sub>EBO</sub>	emitter-base voltage	open collector	—	7.0	V
I <sub>C</sub>	collector current (DC)		—	6.0	A
I <sub>B</sub>	Base Current		—	3.0	A
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C; note 1	—	2	W
T <sub>stg</sub>	storage temperature		-65	+150	°C
T <sub>j</sub>	junction temperature		—	150	°C
T <sub>amb</sub>	operating ambient temperature		-65	+150	°C

**Note**

1. Transistor mounted on an FR4 printed-circuit board.

## RATING CHARACTERISTIC CURVES ( CHT3055ZPT )

### CHARACTERISTICS

$T_{amb} = 25\text{ }^{\circ}\text{C}$  unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$I_{CEO}$	collector cut-off current	$V_{CE}=30\text{ V}$	–	700	$\mu\text{A}$
$I_{EBO}$	emitter cut-off current	$V_{EB}=7.0\text{V}$	–	5.0	mA
$h_{FE}$	DC current gain	$I_C = 4.0\text{A}; V_{CE} = 4\text{V}$ $I_C = 6.0\text{A}; V_{CE} = 4\text{V}$	20 5.0	70 –	
$V_{CEsat}$	collector-emitter saturation voltage	$I_C=4.0\text{A}, I_B=400\text{mA}$	–	1.1	V
$V_{BEON}$	base-emitter saturation voltage	$I_C = 4.0\text{A}; V_{CE} = 4\text{V}$	–	1.5	V
$f_T$	transition frequency	$I_C = 500\text{mA}; V_{CE} = 10\text{ V};$ $f = 1.0\text{MHz}$	2.5	–	MHz